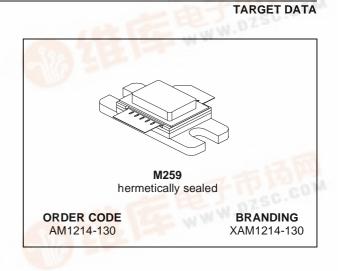
AM1214-130 RF POWER TRANSISTORS L-BAND RADAR APPLICATIONS

- REFRACTORY /GOLD METALLIZATION
- EMITTER SITE BALLASTING
- LOW RF THERMAL RESISTANCE
- INPUT/OUTPUT MATCHING
- OVERLAY GEOMETRY

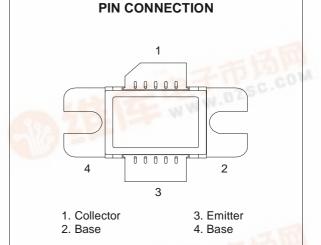
- METAL/CERAMIC HERMETIC PACKAGE
- POUT = 130 W MIN. WITH 8.0 dB GAIN
- 1215-1400 MHz OPERATION



DESCRIPTION

The AM1214-130 is a rugged, Class C common base device designed as driver of AM1214-250 for new L - Band medium & long pulse radar applications.

Minimal amplitude droop over a long pulse of 500 microsec. is guaranteed by a thermal design incorporating an overlay site-ballasted die geometry.



ABSOLUTE MAXIMUM RATINGS (Tease = 25° C)

ABSOLUTE MAXIMUM (ATTINGS (TCASE - 23 C)					
Symbol	Parameter	Value	Unit		
P _{DISS}	Power Dissipation $(T_C \le 85^{\circ}C)^*$	TBD	W		
Ι _C	Device Current*	12	A		
V _{CBO}	Collector-Base Voltage	70	V		
Тj	Operating Junction Temperature	+250	°C		
T _{STG}	Storage Temperature	-65 to +200	°C		

THERMAL DATA

R _{th(j-c)}	Junction -Case Thermal Resistance*	TBD	°C/W

 * Applies only to rated RF amplifier operation: 150 microsec / 10%



AM1214-130

ELECTRICAL SPECIFICATION (T_{CASE} = 25°C)

STATIC

Symbol		Test Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 20 mA	I _E = 0 mA	70			V
BV _{CES}	I _C = 20 mA	$V_{BE} = 0 V$	70			V
BV _{EBO}	I _E = 10 mA	$I_{\rm C} = 0 \rm{mA}$	3.5			V
I _{CES}	V _{CE} = 40 V	$V_{BE} = 0 V$			5	mA
h _{FE}	V _{CE} = 5 V	I _C = 0.25 A	10			

DYNAMIC @ 150 MICROSEC / 10 %

Symbol	Test Conditions				Тур.	Max.	Unit
POUT	f = 1215 - 1400 MHz	P _{IN} = 20 W	$V_{CC} = 50 V$	130	160		W
ης	f = 1215 - 1400 MHz	P _{IN} = 20 W	$V_{CC} = 50 V$	40	45		%
GP	f = 1215 - 1400 MHz	P _{IN} = 20 W	V _{CC} = 50 V	8.1	9.0		dB

DYNAMIC @ 500 MICROSEC / 10 %

Symbol	Test Conditions				Тур.	Max.	Unit
Pout	f = 1215 - 1400 MHz	P _{IN} = 20 W	$V_{CC} = 50 V$	110	140		W
ηс	f = 1215 - 1400 MHz	P _{IN} = 20 W	$V_{CC} = 50 V$	40	45		%
GP	f = 1215 - 1400 MHz	P _{IN} = 20 W	$V_{CC} = 50 V$	7.4	8.45		dB

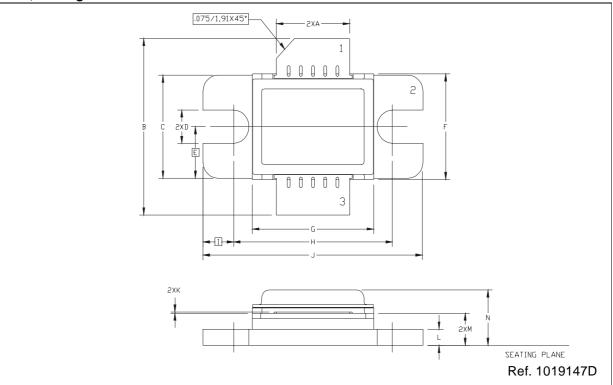
AM1214-130

ым	mm			Inch			
DIM.	MIN.	TYP.	MAX	MIN.	TYP.	MAX	
А	7.49		7.75	.295		.305	
В	19.56		21.08	.770		.830	
С	9.65		9.91	.380		.390	
D	3.18		3.43	.125		.135	
E		4.90			.193		
F	10.03		10.34	.395		.407	
G	12.45		12.95	.490		.510	
Н	16.38		16.64	.645		.655	
I		3.18			.125		
J	22.61		23.11	.890		.910	
К	0.05		0.15	.002		.006	
L	1.40		1.65	.055		.065	
М	2.79		3.30	.110		.130	
Ν			5.84			.230	

M259 (.400 x .500 SUPER WIDE 2/L HERM. W/FLG) MECHANICAL DATA

M259, Package Outline

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